

N-Channel Silicon Junction Field-Effect Transistor

• Low-Noise, High Gain Amplifier

Absolute maximum ratings at $T_A = 25^\circ\text{C}$

Reverse Gate Source & Reverse Gate Drain Voltage	- 20 V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	225 mW
Power Derating	1.8 mW/°C
Storage Temperature Range	- 65°C to 200°C

At 25°C free air temperature:

Static Electrical Characteristics

		IF1330		Process NJ132H		
		Min	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	- 20		V	$I_G = -1\ \mu\text{A}, V_{DS} = \emptyset\text{V}$	
Gate Reverse Current	I_{GSS}		- 0.1	nA	$V_{DS} = \emptyset\text{V}, V_{GS} = -10\text{V}$	
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	- 0.35	- 1.5	V	$V_{DS} = 10\text{V}, I_D = 0.5\ \text{mA}$	
Drain Saturation Current (Pulsed)	I_{DSS}	5	20	mA	$V_{DS} = 10\text{V}, V_{GS} = \emptyset\text{V}$	

Dynamic Electrical Characteristics

Common Source Forward Transconductance	g_{fs}	10		mS	$V_{DS} = 10\text{V}, I_D = 5\ \text{mA}$	$f = 1\ \text{kHz}$
Common Source Input Capacitance	C_{iss}		20	pF	$V_{DS} = 10\text{V}, I_D = 5\ \text{mA}$	$f = 1\ \text{MHz}$
Common Source Reverse Transfer Capacitance	C_{rss}		5	pF	$V_{DS} = 10\text{V}, I_D = 5\ \text{mA}$	$f = 1\ \text{MHz}$

Typ

Equivalent Short Circuit Input Noise Voltage	\bar{e}_N	2.5		nV/√Hz	$V_{DS} = 10\text{V}, I_D = 5\ \text{mA}$	$f = 1\ \text{kHz}$
--	-------------	-----	--	--------	---	---------------------

TO-236AB Package
Dimensions in Inches (mm)

Pin Configuration
1 Drain, 2 Source, 3 Gate

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.